

www.vishay.com

### Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 50 A



PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	50 A					
$V_{DRM}/V_{RRM}$	1200 V					
V <sub>TM</sub> (typ.)	1.1 V					
I <sub>GT</sub> (typ.)	35 mA					
$T_J$	-40 °C to +150 °C					
Package	TO-247AD 3L					
Circuit configuration	Single SCR					

#### **FEATURES**

 Designed and qualified according 1 JEDEC®-JESD 47



**FREE** 

Low I<sub>GT</sub> designed

• 150 °C maximum operating junction temperature

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V					
V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.1	V					
I <sub>T(AV)</sub>		50						
I <sub>RMS</sub>		79	Α					
I <sub>TSM</sub>		630						
dV/dt		500	V/µs					
T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C					

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-50TPS12AL-M3	1200	1300	10					



ABSOLUTE MAXIMUM RATING	S					
DADAMETED	SYMBOL	(MBOL TEST CONDITIONS		VALUES		UNITS
PARAMETER	STWIDUL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 112 °C, 180° conduction half sine wave		-	50	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			1	79	А
Peak, one-cycle non-repetitive surge current	l	10 ms sine pulse, rated V <sub>RRM</sub> applied		1	530	
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied Initia	al $T_J = T_J$	ı	630	
12t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied max	imum	-	1405	A <sup>2</sup> s
I <sup>2</sup> t for fusing	I-t	10 ms sine pulse, no voltage reapplied			1986	A-S
$I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied, T <sub>J</sub> = 125 °C		-	19 850	A <sup>2</sup> √s
Low level value of threshold voltage	V <sub>T(TO)1</sub>			-	0.89	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	T <sub>J</sub> = 125 °C		-	0.97	V
Low level value of on-state slope resistance	r <sub>t1</sub>	1J= 125 C		-	6.77	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>			-	6.32	11152
On atota valtage	V	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V
On-state voltage	V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C			1.6	V
Rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		-	150	A/µs
Holding current	I <sub>H</sub>	Anada aumilia G.V. registive load T. OF °C		-	300	
Latching current	ΙL	Anode supply = 6 V, resistive load, $T_J = 25 ^{\circ}\text{C}$		-	350	mA
Deverge and direct leakage current	1 /1	T <sub>J</sub> = 25 °C		-	0.05	111/4
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			10	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$ - $k = 1$	100 Ω	-	500	V/µs

TRIGGERING								
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS		
Peak gate power	$P_{GM}$	10 ma sina nula	se, no voltage reapplied	-	10	W		
Average gate power	P <sub>G(AV)</sub>	TO THS SINE PUIS	e, no voltage reapplied	-	2.5	] vv		
Peak gate current	I <sub>GM</sub>			-	2.5	Α		
Peak negative gate voltage	-V <sub>GM</sub>			-	10			
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load		1.6	V		
Required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		-	1.5	ľ		
		T <sub>J</sub> = 150 °C		-	1			
		T <sub>J</sub> = -40 °C		-	100			
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	35	60	mA		
		T <sub>J</sub> = 150 °C		-	40			
DC gate voltage not to trigger	$V_{GD}$	T <sub>.I</sub> = 150 °C, V <sub>DBM</sub> = rated value		-	0.15	V		
DC gate current not to trigger	I <sub>GD</sub>	$I_J = 150^{\circ}C, V_D$	RM = rated value	-	2.5	mA		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Turn-on time	t <sub>gt</sub>	$I_T = 50 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 ^{\circ}\text{C}$	1.5	
Turn-off time	t <sub>q</sub>	$\begin{array}{l} I_T = 50 \text{ A, V}_D = 80 \text{ \% V}_{DRM},  dV/dt = 20 \text{ V/}\mu\text{s, t}_p = 200  \mu\text{s} \\ I_{gt} = 100 \text{ mA, dI/dt} = 10  A/\mu\text{s, V}_R = 100  \text{V, T}_J = 150  ^{\circ}\text{C} \end{array}$	92	μs



THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS		MAX.	UNITS		
Maximum junction and storag	e temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 15		°C		
Maximum thermal resistance,	imum thermal resistance, junction to case			-	0.35			
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		-	40	°C/W		
Typical thermal resistance, ca	Typical thermal resistance, case to heatsink		Mounting surface, smooth, and greased	0.2	-			
Mounting torque	minimum			6	(5)	kgf · cm		
Mounting torque	maximum			12	(10)	(lbf $\cdot$ in)		
Marking device			Case style Super TO-247AD 3L	,	50TPS12A	۱L		

∆R <sub>thJ-HS</sub> CONDU	JCTION	PER JU	INCTIO	N							
DEVICE	S	SINE HALF-WAVE CONDUCTION					ION RECTANGULAR WAVE CONDUCTION				LIMITO
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

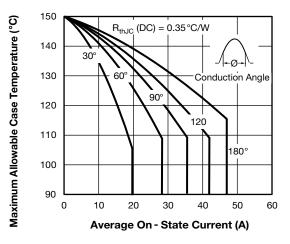


Fig. 1 - Current Rating Characteristics

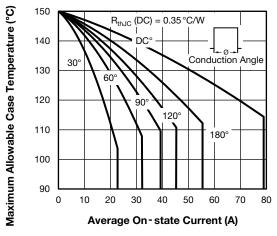


Fig. 2 - Current Rating Characteristics

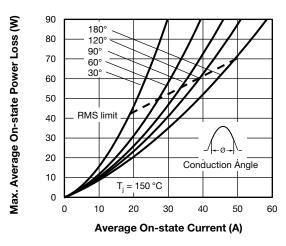


Fig. 3 - On-State Power Loss Characteristics

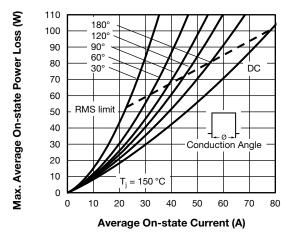


Fig. 4 - On-State Power Loss Characteristics

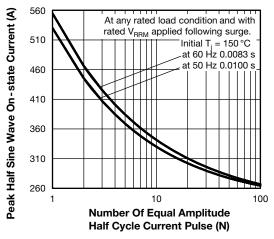


Fig. 5 - Maximum Non-Repetitive Surge Current

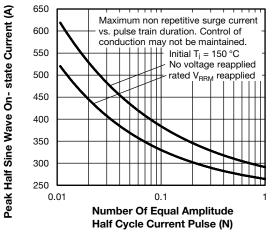


Fig. 6 - Maximum Non-Repetitive Surge Current

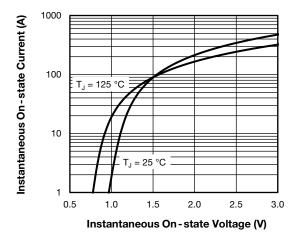


Fig. 7 - On-State Voltage Drop Characteristics

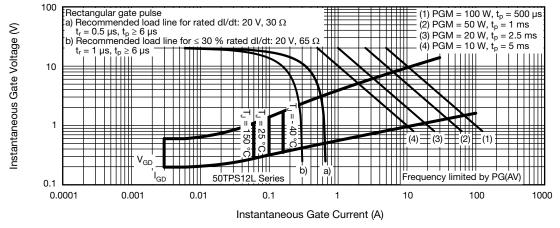


Fig. 8 - Gate Characteristics

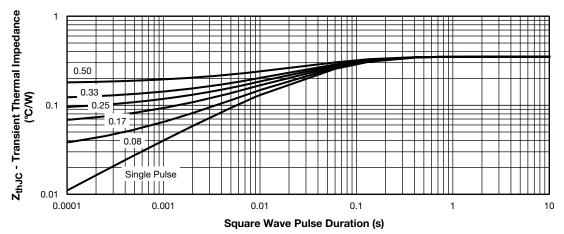


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

#### **ORDERING INFORMATION TABLE**

Device code	VS-	50	Т	Р	s	12	Α	L	-М3
			3		(5)	6	7	8	

Vishay Semiconductors product

Current code (50 = 50 A)

Circuit configuration:

T = thyristor

P = TO-247AD 3L package

Type of silicon:

S = standard recovery rectifier

Voltage code (12 = 1200 V)

A = Low I<sub>GT</sub> selection

Package L = long lead

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

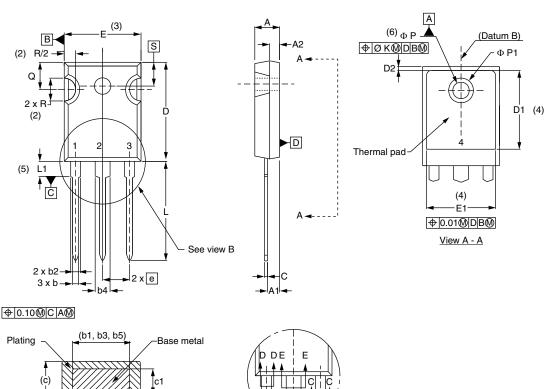
ORDERING INFORMATION (example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-50TPS12AL-M3	25	500	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				



### **TO-247AD 3L**

#### **DIMENSIONS** in millimeters and inches



Section C - C, D - D, E - E									
SYMBOL	MILLIN	IETERS	INC	HES	NOTES				
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES				
Α	4.65	5.31	0.183	0.209					
A1	2.21	2.59	0.087	0.102					
A2	1.50	2.49	0.059	0.098					
b	0.99	1.40	0.039	0.055					

0.039

0.065

0.065

0.102

0.102

0.015

0.015

0.776

0.515

0.053

0.094

0.092

0.135

0.133

0.035

0.033

0.815

(h h2 h4)

:5	

View B

SYMBOL	MILLIMILILIA		INCLIES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØΚ	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		
•	•		•		•

INCHES

MILLIMETERS

#### Notes

b1

b2

b3

b4

b5

С

с1

D

D1

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

1.35

2.39

2.34

3.43

3.38

0.89

0.84

20.70

- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

3

- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1

0.99

1.65

1.65

2.59

2.59

0.38

0.38

19.71

13.08

- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



### **Legal Disclaimer Notice**

Vishay

#### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.